



**ALPHA & OMEGA**  
SEMICONDUCTOR

**AOC2415**

**20V P-Channel MOSFET**

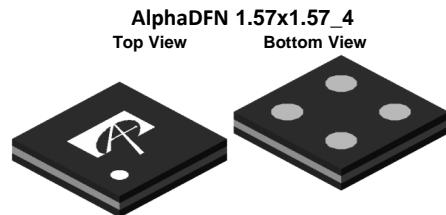
### General Description

The AOC2415 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.5V while retaining a 8V  $V_{GS(MAX)}$  rating.

### Product Summary

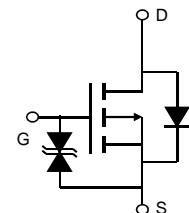
$V_{DS}$	-20V
$I_D$ (at $V_{GS}=-4.5V$ )	-3.5A
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$ )	< 33mΩ
$R_{DS(ON)}$ (at $V_{GS}=-2.5V$ )	< 38mΩ
$R_{DS(ON)}$ (at $V_{GS}=-1.8V$ )	< 45mΩ
$R_{DS(ON)}$ (at $V_{GS}=-1.5V$ )	< 54mΩ

Typical ESD protection      HBM Class 3A



Top View

Bottom View



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Source Current (DC) <sup>Note1</sup>	$I_D$	-3.5	A
Source Current (Pulse) <sup>Note2</sup>	$I_{DM}$	-50	
Power Dissipation <sup>Note1</sup>	$P_D$	0.55	W
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup> $t \leq 10s$	$R_{θJA}$	140	170	°C/W
Maximum Junction-to-Ambient <sup>A,D</sup> Steady-State		190	230	°C/W

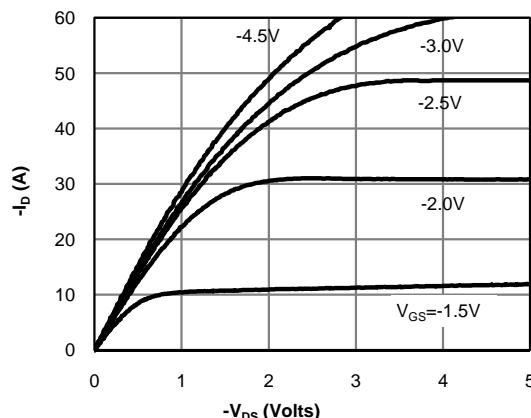
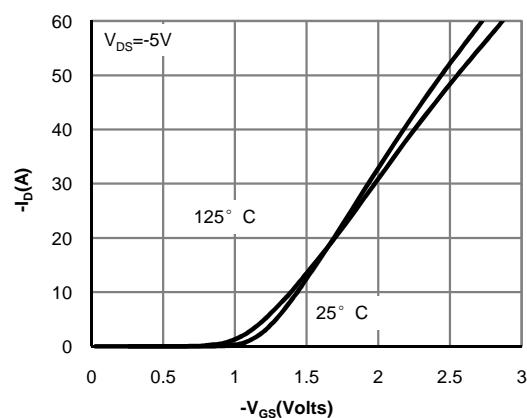
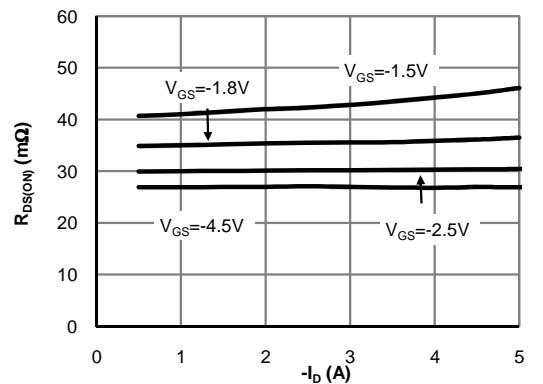
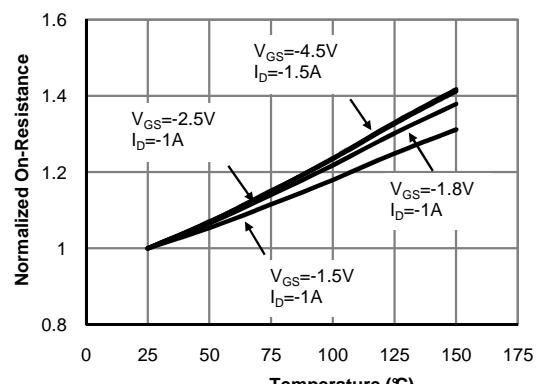
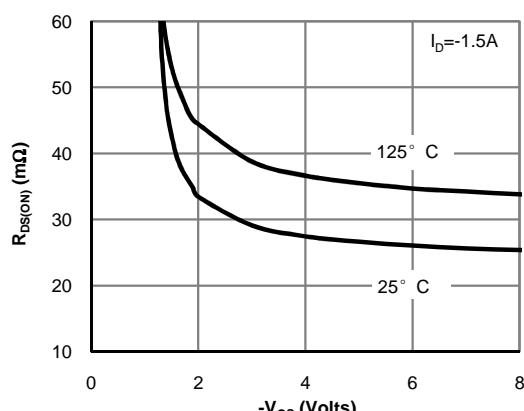
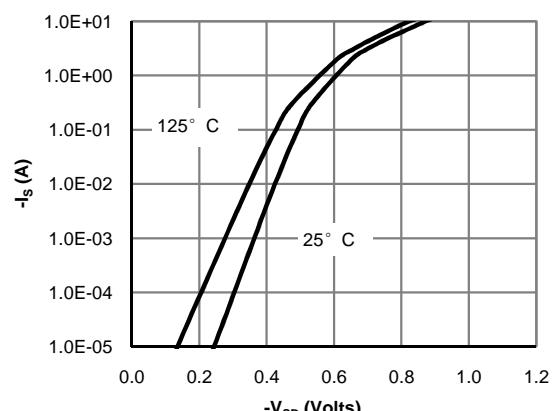
**Note 1.** Mounted on minimum pad PCB

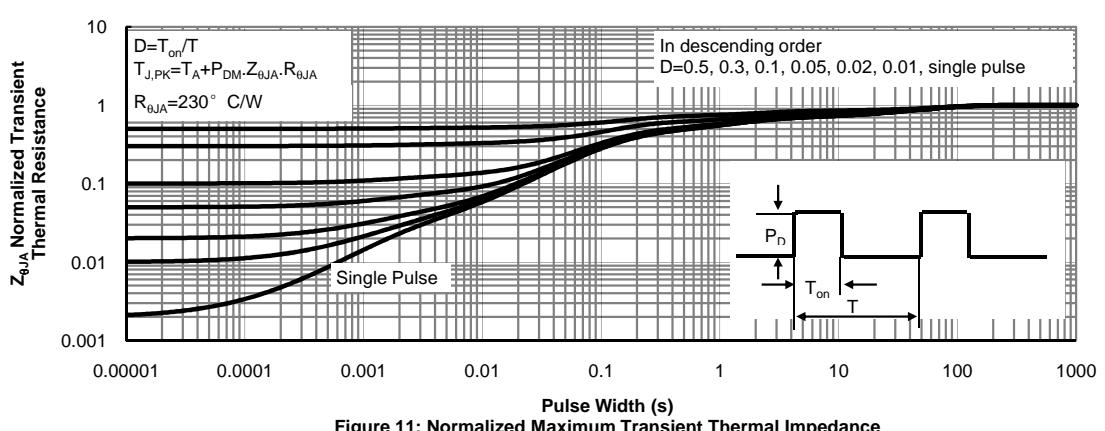
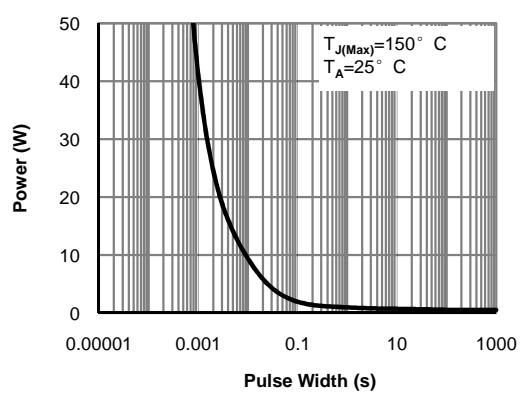
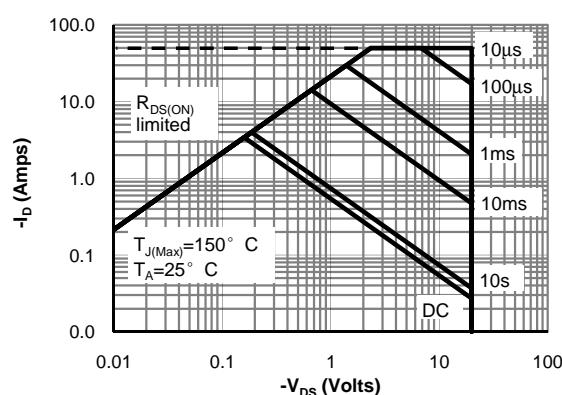
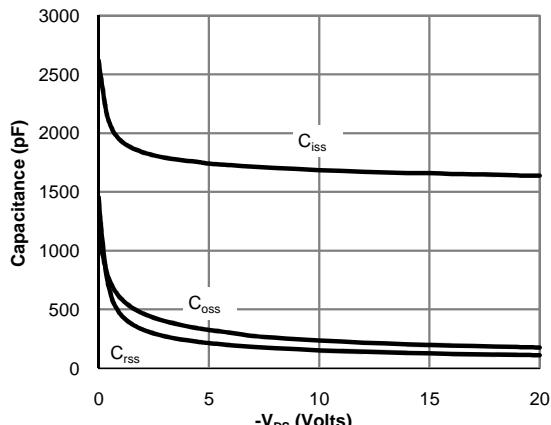
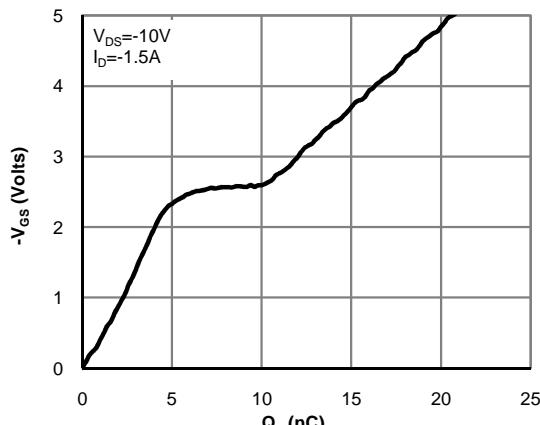
**Note 2.** PW <300 μs pulses, duty cycle 0.5% max

**Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)**

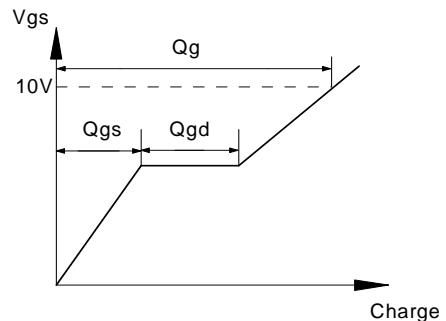
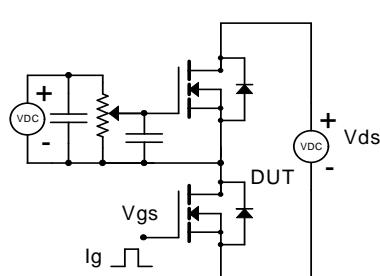
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-20			V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS}=-20\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 8\text{V}$			$\pm 10$	$\mu\text{A}$
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.3	-0.65	-1.0	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}, I_D=-1.5\text{A}$ $T_J=125^\circ\text{C}$	27	33		$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-1\text{A}$	36	44		$\text{m}\Omega$
		$V_{GS}=-1.8\text{V}, I_D=-1\text{A}$	30	38		$\text{m}\Omega$
		$V_{GS}=-1.5\text{V}, I_D=-1\text{A}$	35	45		$\text{m}\Omega$
$g_{\text{FS}}$	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-1.5\text{A}$		14		S
$V_{\text{SD}}$	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.6	-1	V
<b>DYNAMIC PARAMETERS</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$		1685		pF
$C_{\text{oss}}$	Output Capacitance			235		pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			150		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		1.3		$\text{k}\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, I_D=-1.5\text{A}$		19	28	nC
$Q_{\text{gs}}$	Gate Source Charge			5		nC
$Q_{\text{gd}}$	Gate Drain Charge			5.5		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, R_L=6.67\Omega, R_{\text{GEN}}=3\Omega$		0.65		$\mu\text{s}$
$t_r$	Turn-On Rise Time			1.1		$\mu\text{s}$
$t_{\text{D(off)}}$	Turn-Off Delay Time			4		$\mu\text{s}$
$t_f$	Turn-Off Fall Time			3.8		$\mu\text{s}$
$t_{\text{rr}}$	Body Diode Reverse Recovery Time	$I_F=-1.5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		16		ns
$Q_{\text{rr}}$	Body Diode Reverse Recovery Charge	$I_F=-1.5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		9		nC

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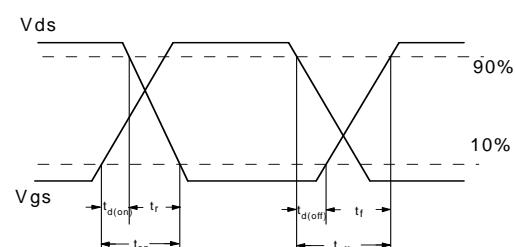
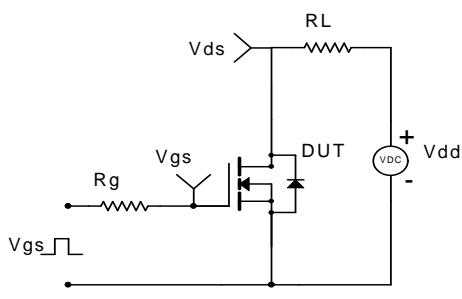
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Fig 1: On-Region Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**

**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

**Figure 6: Body-Diode Characteristics (Note E)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**


### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms



### Diode Recovery Test Circuit & Waveforms

